

CMKSH-3T
SURFACE MOUNT
ULTRAmimi™
TRIPLE ISOLATED
SILICON SCHOTTKY DIODES



Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKSH-3T type contains three (3) Isolated Silicon Schottky Diodes, epoxy molded in a SOT-363 surface mount package. This ULTRAmimi™ device has been designed for switching applications requiring a low forward voltage drop.

MARKING CODE: KHT

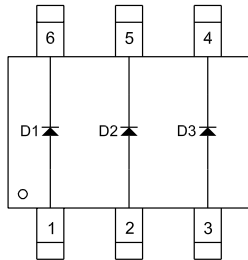
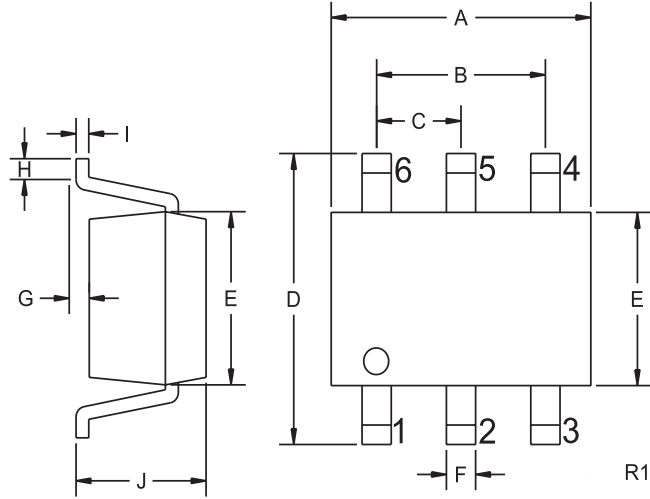
MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _R RM	30	V
Continuous Forward Current	I _F	100	mA
Peak Repetitive Forward Voltage	I _F RM	350	mA
Forward Surge Current, tp=10ms	I _F SM	750	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
B _V R	I _R =100μA	30			V
V _F	I _F =2.0mA		0.29	0.33	V
V _F	I _F =15mA		0.40	0.45	V
V _F	I _F =100mA		0.74	1.00	V
I _R	V _R =25V		90	500	nA
I _R	V _R =25V, T _A =100°C		25	100	μA
C _T	V _R =1.0V, f=1 MHz		7.0		pF
t _{rr}	I _F =I _R =10mA, I _{rr} =1.0mA, R _L =100Ω			5.0	ns

SOT-363 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

LEAD CODE:

- 1) ANODE D1
- 2) ANODE D2
- 3) ANODE D3
- 4) CATHODE D3
- 5) CATHODE D2
- 6) CATHODE D1

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